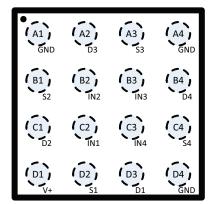
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Vishay Siliconix

ORDERING INFORMATION								
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE	REEL QUANTITY			
DG2501DB-T2-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2501DB-T4-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			
DG2502DB-T2-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2502DB-T4-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			
DG2503DB-T2-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2503DB-T4-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			

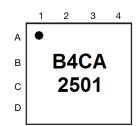
PACKAGE OUTLINE



Top View (Bump Side Down)

Fig. 1 - Package Outline for WCSP16, 1.44 mm x 1.44 mm, 0.35 mm Pitch

DEVICE MARKING



Row 1 Dot = Pin A1 Locator

Row 2 B = Fab, 4 = Year, C = Week Code, A = Lot Code

Row 3 2501 = Part Code

Fig. 2 - Device Marking

ABSOLUTE MAXIMUM RATINGS							
ELECTRICAL PARAMETERS	CONDITIONS	LIMITS	UNIT				
V+, INx	Reference to GND	-0.3 to +6	V				
Sx, Dx	Reference to GND	-0.3 to (V+) +0.3] v				
Maximum continuous switch current		5					
Maximum peak current (Pulsed 1 ms, 10 % duty cycle)		20	mA				
Thermal resistance		80	°C/W				
Latch up current	JESD78	> 800	mA				
ESD - HBM	ANSI / ESDA / JEDEC® JS-001	> 8000	V				
Temperature							
Operating temperature		-40 to +85	• °C				
Storage temperature		-65 to +150					

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



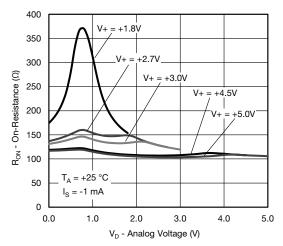
		TEST CONDITION	ı		-40 °C t	o +85 °C	UNIT
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 3 V	TEMP. b	TYP. c	MIN. d	MAX. d	
		V _{INH} = 1.4 V, V _{INL} = 0.4 V ^a					
Analog Switch					1	1 . 1	
Analog signal range e	V _{ANALOG}		Full	-	0	3	V
Drain-source on resistance	R _{DS(on)}		Room Full	133	-	200 250	Ω
On-resistance matching	ΔR_{on}	$V_S = 1.5 \text{ V}, I_S = -1 \text{ mA}$	Room	0.83	-	10	
			Full	-	-	13	
Switch off leakage current	I _S /I _{D(off)}	V+ = 3.3 V, $V_S = 0.3 \text{ V/3 V}, V_D = 3 \text{ V} / 0.3 \text{ V}$	Room	± 0.016	-0.4	+0.4	
			Full	- 0.000	-1	+1	nA
Channel on leakage current	I _{D(on)}	V+ = 3.3 V, $V_D = 0.3 V / 3 V$	Room Full	± 0.009	-0.4 -1	+0.4	
Digital Control		The side type t	ruii		-1	+1	
Input, high voltage	V _{INH}		Full	_	1.4	-	
Input, low voltage	VINH		Full		-	0.4	V
input, low voltage	I _{IN}	V _{IN} = V _{GND} or V+	Room	± 0.001	-	-	μΑ
Input leakage			Full	-	-0.1	+0.1	
Digital input capacitance e	C _{IN}	f = 1 MHz	Room	2	-	-	pF
Dynamic Characteristics			•				
Dunals hafava malsa tima	t _{BBM}	DG2503 only, $V_{S1} = V_{S2} = 1.5 \text{ V}$,	Room	47	10	-	- ns
Break-before make time		$R_L = 300 \Omega C_L = 35 pF$	Full	ı	10	-	
Turn-on time	t _{ON}		Room	175	-	220	
Turr-on time		$V_{S} = 1.5 \text{ V}, R_{L} = 300 \Omega, C_{L} = 35 \text{ pF}$	Full	-	-	250	
Turn-off time		νς = 1.5 ν, τι <u>ς</u> = 550 32, σ <u>ς</u> = 55 μι	Room	77	-	100	
Turri on time			Full	-	-	120	
Charge injection e	Q_{INJ}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 1.5 \text{ V}$	Room	-0.7		-	рС
Off isolation e	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f = 1MHz$	Room	-83	-	-	dB
Cross talk ^e	X Talk	1 1 - 30 32, OL - 3 β1 , 1 - 1101112	Room	-85	-	-	
3 dB bandwidth ^e	BW	$R_L = 50 \Omega$, $C_L = 5 pF$	Room	510	-	-	MH
Source off capacitance e	C _{S(off)}		Room	2.9	-	-	_
Drain off capacitance e	C _{D(off)}	f = 1 MHz, V _S = 1.5 V	Room	2.8	-	-	pF
Drain on capacitance e	C _{D(on)}		Room	7.8	-	-	
Power Requirements							
Power supply current	l+	Digital input 0 or V+	Room	0.001	-	-	μA
i owoi suppiy cuitetit	'+	Digital input 0 of VT	Full	-	=.	1	

ELECTRICAL CHARACTERISTICS 5 V Supply								
		TEST CONDITION	TEMP. b	TYP.°	-40 °C to +85 °C			
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 5 V			MIN. d	MAX. d	UNIT	
		$V_{INH} = 1.8 \text{ V}, V_{INL} = 0.5 \text{ V}^{a}$			Willy.	IVIAX. 4		
Analog Switch								
Analog signal range e	V_{ANALOG}		Full	-	0	5	V	
Drain-source on resistance	R _{DS(on)}		Room	104	-	150	Ω	
Brain oddrod dirrodiotariod	. 103(011)	$V_S = 2.5 \text{ V}, I_S = -1 \text{ mA}$	Full	-	-	200		
On-resistance matching	ΔR_{on}	13 =15 1, 13	Room	0.39	-	8		
	OII		Full	-	-	10		
Switch off leakage current	I _S /I _{D(off)}	V+ = 5.5 V,	Room	± 0.022	-0.4	+0.4		
	()	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}$	Full	-	-1	+1	nA	
Channel on leakage current	I _{D(on)}	V+ = 5.5 V, $V_D = 4.5 V/1 V$	Room	± 0.017	-0.4	+0.4		
		VD = 4.3 V/ 1 V	Full	-	-1	+1		
Digital Control	W		Full	_	1.8	l <u>-</u> I		
Input, high voltage	V _{INH}		Full	_	1.0	0.5	V	
Input, low voltage	V _{INL}		Room	± 0.001	_		μΑ	
Input leakage	I _{IN}	$V_{IN} = V_{GND}$ or V+	Full	± 0.001	-1	+1		
Digital input capacitance e	C _{IN}	f = 1 MHz	Room	2	-	-	pF	
Dynamic Characteristics	Olld	1 - 1 1/11/12	Hoom				Pi	
-		DG2503 only, V _{S1} = V _{S2} = 3 V,	Room	25	10	I - I		
Break-before make time	t _{BBM}	$R_L = 300 \Omega C_L = 35 pF$	Full	-	10	-		
	t _{ON}		Room	64	-	100	ns	
Turn-on time		V 0V D 000 0 0 05 . F	Full	-	-	150		
T		$V_S = 3 \text{ V}, R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room	38	-	60		
Turn-off time	t _{OFF}		Full	-	-	100		
Charge injection ^e	Q _{INJ}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 3 \text{ V}$	Room	-2	-	-	рС	
Off isolation ^e	OIRR	P. = 50 O. C. = 5 pE f = 1MU =	Room	-84	-	-	40	
Cross talk e	X Talk	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-83	-	-	dB	
3 dB bandwidth e	BW	$R_L = 50 \Omega, C_L = 5 pF$	Room	550	-	-	MHz	
Source off capacitance e	C _{S(off)}		Room	2.7	-	-		
Drain off capacitance e	C _{D(off)}	$f = 1 MHz, V_S = 3 V$	Room	2.6	-	-	рF	
Drain on capacitance e	C _{D(on)}		Room	7.6	-	-		
Power Requirements								
		Digital input = 1.8 V, at one channel	Room	4.6	-	-		
Power supply current	I+	V+ = 5 V	Full	-	-	30	μΑ	
i owei suppiy cuitetit	1+	Digital input 0 or V+	Room	0.001	-	-		
		Digital hipat o of VF	Full	-	-	2		

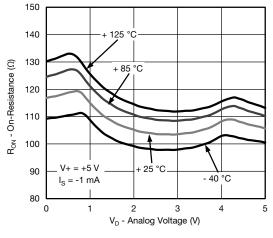
Notes

- a. V_{IN} = input voltage to perform proper function
- b. Room = 25 °C, Full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The convention where the most negative value is a minimum and the most positive a maximum, is used in this data sheet
- e. Guaranteed by design, not subject to production test

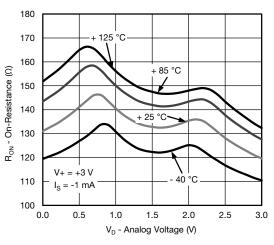
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



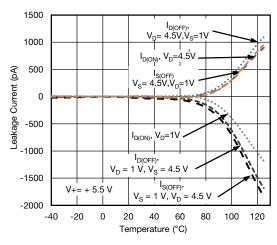
On-Resistance vs. Analog Voltage



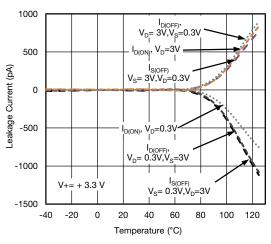
On-Resistance vs. Analog Voltage



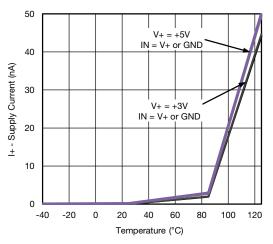
On-Resistance vs. Analog Voltage



Leakage Current vs. Temperature

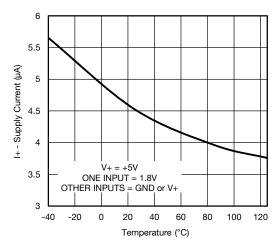


Leakage Current vs. Temperature

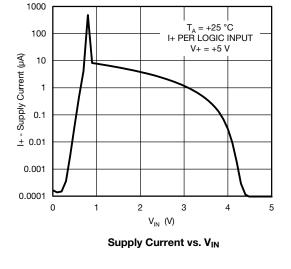


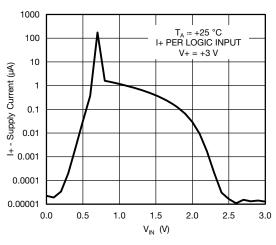
Supply Current vs. Temperature

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

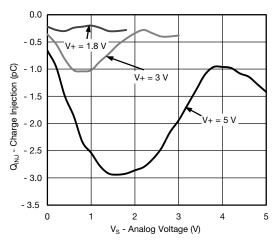


Supply Current vs. Temperature

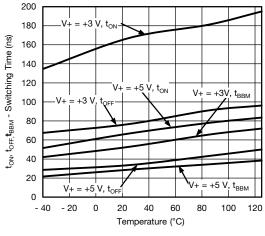




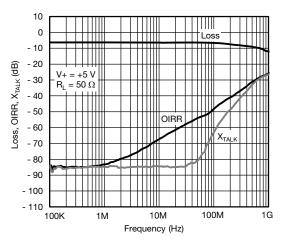
Supply Current vs. VIN



Charge Injection vs. Analog Voltage

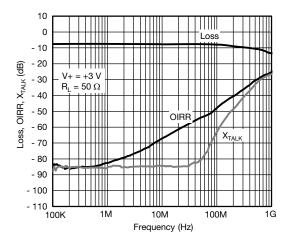


Switching Time vs. Temperature

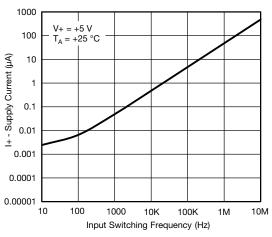


Loss, OIRR, X_{TALK} vs. Frequency

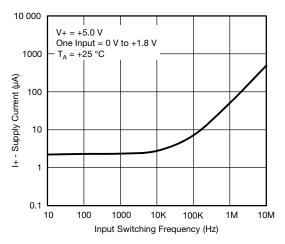
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



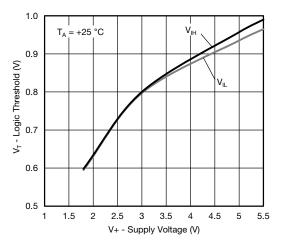
Loss, OIRR, X_{TALK} vs. Frequency



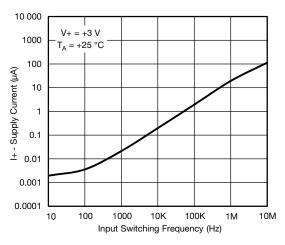
Supply Current vs. Input Switching Frequency



Supply Current vs. Input Switching Frequency

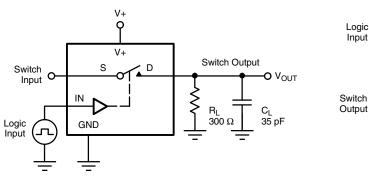


Logic Threshold vs. Supply Voltage



Supply Current vs. Input Switching Frequency

TEST CIRCUIT



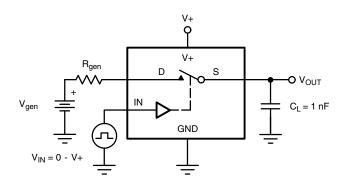
VINH $\begin{array}{c} V_{\text{INH}} \\ V_{\text{INL}} \\ \\ 0 \ V \\ \\ t_{\text{ON}} \\ \end{array}$

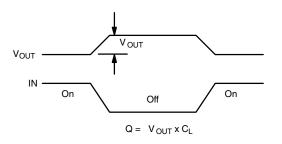
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_D \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

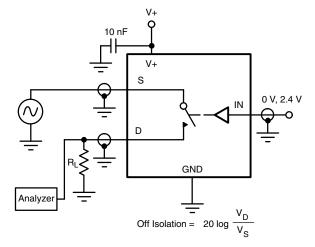
Fig. 3 - Switching Time





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 4 - Charge Injection



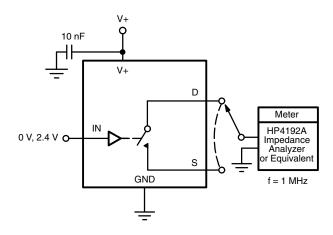


Fig. 5 - Off-Isolation

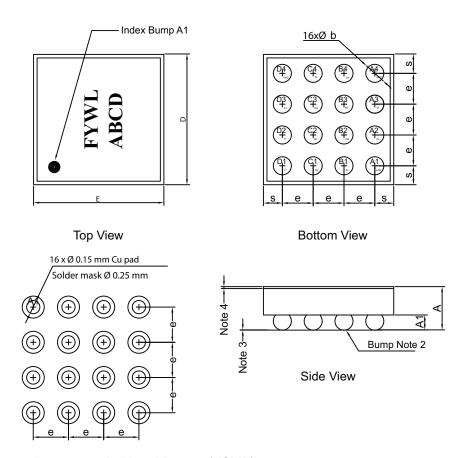
Fig. 6 - Channel Off/On Capacitance

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WCSP 4 x 4: 16 Bumps

(4 x 4, 0.35 mm pitch, 172 μm bump height, 1.48 mm x 1.48 mm die size)



Recommended Land Pattern (NSMD)

DWG: 6022

Notes

- (1) Laser mark on the silicon die back, coated with an epoxy film
- (2) Bumps are SAC405
- (3) 0.05 max. co-planarity
- (4) Laminate tape thickness is 0.022 mm

DIM.	MILLIMETERS ^a			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.444	0.474	0.504	0.0175	0.0187	0.0198	
A1	0.146	0.172	0.198	0.0057	0.0068	0.0078	
b	0.165	0.205	0.245	0.0065	0.0081	0.0096	
е		0.350			0.0138		
s	0.175	0.195	0.215	0.0069	0.0077	0.0085	
D	1.400	1.440	1.480	0.0551	0.0567	0.0583	
E	1.400	1.440	1.480	0.0551	0.0567	0.0583	

Note

a. Use millimeters as the primary measurement.

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Vishay

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